BUNKOUKEIKI Model CMM-250

High Sensitivity Carrier Mobility Measurement System



The Model CMM-250 has been designed to measure the electron and hole mobilities which are very critical to evaluation of the thin film to be used for the EL elements and solar cells. The system consists of a short pulse nitrogen excitation die laser for carrier generation, high speed sampling electronics, sample compartment and data processing system. Our noise prevention measures and unique signal processing have reduced noise significantly so that fast response such as nano-second order and high detection sensitivity have been achieved in order to measure the electron and hole mobilities. Changing different die (as an option) of the die laser enables the system to oscillate the wavelength range from 337nm to 730nm with pulse width shortened in 600 pico second. In addition to this TOF method measurement, the system with an optional unit is capable to measure mobilities by FET method.

Features

- Achievement of time resolution at nano-second enables the system to measure mobility such as 10⁻⁷-10⁻¹cm²/V·sec.
- Easy Operation with probe/sample compartment
- New designed optics and data processing enabled to obtain high SN ratio data

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Measurement

Mobility calculation

While checking the measurement data, mobility can be easily calculated.

By putting cursor on the inflection point, mobility can be calculated automatically while seeing the logarithmic converted data.



Signal processing

In addition to noise prevention, our unique signal processing enables the system to calculate very small signal data with large noise. The measurement can be applied to the thinner film or high mobility sample, which extends the measurement range.



FET Measurement (Option)

Installing the optional probe and software,the system is enabled to measure mobility measurement for FET type element.



Specifications

Light source: nitrogen excitation die laser Nitrogen laser pulse width: 600psec Nitrogen laser output: 250KW@10Hz Output wavelength: 337.1nm $360 \sim 720$ nm (die is optional) Die laser pulse width: 400psec at 480nm Measurement time resolution: less than 10 nsec Measurement mobility range: 10-7 ~ 10-1cm $2/V \cdot$ sec Bias voltage : $0 \sim \pm 500V$ Load resistance: $50\Omega \sim 100$ K Ω 5 steps

Y axis time resolution: 8 bits (11 bits in averaging) Synchronization: Excitation light monitoring system by PIN photodiode Personal computer Laser control : Laser ON/OFF Data acquisition: 1shot ~256 shots Data analysis: Data display, save Y and X axis logarithmic conversion Calculation of transit time and mobility

*Product specifications and external appearance are subject to change without prior notice.

BUNKOUKEIKI CO., LTD.